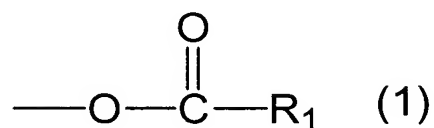


Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) An underlayer coating forming composition comprising a dextrin ester compound that at least 50% of hydroxy groups in dextrin is converted into ester groups of formula (1):



wherein R₁ is C₁₋₁₀alkyl group that may be substituted with hydroxy group, carboxyl group, cyano group, nitro group, C₁₋₆alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C₁₋₆alkoxycarbonyl group, or a phenyl group, a naphthyl group or an anthryl group that may be substituted with C₁₋₆alkyl group, hydroxy group, carboxyl group, cyano group, nitro group, C₁₋₆alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C₁₋₆alkoxycarbonyl group, a crosslinking compound, and an organic solvent.

2. (Original) An underlayer coating forming composition comprising a dextrin ester compound that at least 50% of hydroxy groups in dextrin is converted into ester groups of formula (1) wherein R₁ has the same meaning as that defined in claim 1, and that has a weight average molecular weight of 4000 to 20000, a crosslinking compound, and an organic solvent.

3. (Currently Amended) The underlayer coating forming composition according to claim 1 ~~or 2~~, further comprising an acid compound or an acid generator.

4. (Currently Amended) A method for forming photoresist pattern for use in manufacture of semiconductor device, comprising the steps of:

coating the underlayer coating forming composition according to claim 1 ~~any one of claims 1 to 3~~ on a semiconductor substrate, and baking it to form an underlayer coating; forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.

5. (Currently Amended) The underlayer coating forming composition according to claim 1 ~~or 2~~, in which the composition is used for forming an underlayer coating by coating the composition on a semiconductor substrate having a hole with an aspect ratio shown in height/diameter of 1 or more, and baking it.

6. (New) The underlayer coating forming composition according to claim 2, further comprising an acid compound or an acid generator.

7. (New) A method for forming photoresist pattern for use in manufacture of semiconductor device, comprising the steps of:
coating the underlayer coating forming composition according to claim 2 on a semiconductor substrate, and baking it to form an underlayer coating; forming a photoresist layer on the underlayer coating;
exposing the semiconductor substrate covered with the underlayer coating and the photoresist

layer to light; and

developing the photoresist layer after the exposure to light.

8. (New) A method for forming photoresist pattern for use in manufacture of

semiconductor device, comprising the steps of:

coating the underlayer coating forming composition according to claim 3 on a semiconductor substrate, and baking it to form an underlayer coating; forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.

9. (New) The underlayer coating forming composition according to claim 2, in which the

composition is used for forming an underlayer coating by coating the composition on a

semiconductor substrate having a hole with an aspect ratio shown in height/diameter of 1 or more, and baking it.

10. (New) A method for forming photoresist pattern for use in manufacture of

semiconductor device, comprising the steps of:

coating the underlayer coating forming composition according to claim 6 on a semiconductor substrate, and baking it to form an underlayer coating; forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.